

TOSHIBA Photocoupler GaAs Ired + Photo-Triac

# TLP161J

Triac Drive

Programmable Controllers

Ac-Output Module

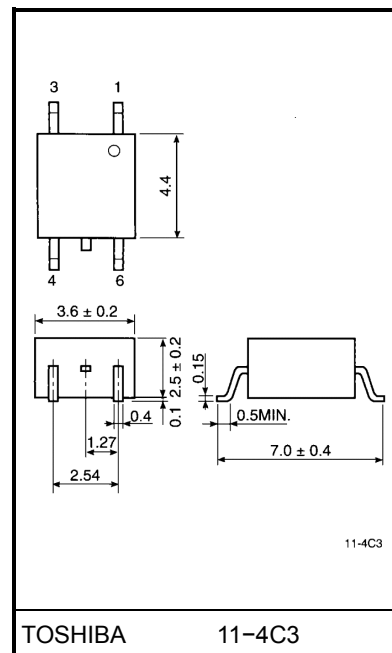
Solid State Relay

The TOSHIBA mini flat coupler TLP161J is a small outline coupler, suitable for surface mount assembly.

The TLP161J consists of a photo triac, optically coupled to a gallium arsenide infrared emitting diode.

- Zero-voltage crossing Turn-on
- Peak off-state voltage: 600V (min.)
- Trigger LED current: 10mA (max.)
- On-state current: 70mA (max.)
- Isolation voltage: 2500Vrms (min.)
- UL recognized: UL1577, file no. E67349

Unit in mm



Weight: 0.09 g

## Trigger LED Current

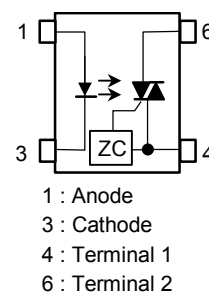
| Classification* | Trigger LED Current (mA)       |      | Marking Of Classification |
|-----------------|--------------------------------|------|---------------------------|
|                 | V <sub>T</sub> = 6V, Ta = 25°C |      |                           |
|                 | Min.                           | Max. |                           |
| (IFT7)          | —                              | 7    | T7                        |
| Standard        | —                              | 10   | T7, blank                 |

\*Ex. (IFT7); TLP161J (IFT7)

(Note) Application type name for certification test, please use standard product type name, i.e.

TLP161J (IFT7): TLP161J

## Pin Configuration



## Maximum Ratings (Ta = 25°C)

| Characteristic                                  |  |           | Symbol               | Rating  | Unit    |
|---|--|-----------|----------------------|---------|---------|
| LED   | Forward current  |           | I <sub>F</sub>       | 50      | mA      |
|   | Forward current derating (Ta ≥ 53°C)                   |           | ΔI <sub>F</sub> / °C | −0.7    | mA / °C |
|   | Peak forward current (100μs pulse, 100pps)             |           | I <sub>FP</sub>      | 1       | A       |
|   | Reverse voltage  |           | V <sub>R</sub>       | 5       | V       |
|   | Junction temperature                                   |           | T <sub>j</sub>       | 125     | °C      |
| Detector  | Off-state output terminal voltage                      |           | V <sub>DRM</sub>     | 600     | V       |
|   | On-state RMS current                                   | Ta = 25°C | I <sub>T(RMS)</sub>  | 70      | mA      |
|   |  | Ta = 70°C |                      | 40      |         |
|   | On-state current derating (Ta ≥ 25°C)                  |           | ΔI <sub>T</sub> / °C | −0.67   | mA / °C |
|   | Peak on-state current (100μs pulse, 120pps)            |           | I <sub>TP</sub>      | 2       | A       |
|   | Peak nonrepetitive surge current (PW = 10ms, DC = 10%) |           | I <sub>TSM</sub>     | 1.2     | A       |
|   | Junction temperature                                   |           | T <sub>j</sub>       | 115     | °C      |
| Storage temperature range                       |  |           | T <sub>stg</sub>     | −55~125 | °C      |
| Operating temperature range                     |  |           | T <sub>opr</sub>     | −40~100 | °C      |
| Lead soldering temperature (10 s)               |  |           | T <sub>sol</sub>     | 260     | °C      |
| Isolation voltage (AC, 1min., R.H ≤ 60%) (Note) |  |           | BV <sub>S</sub>      | 2500    | Vrms    |

(Note) Device considered a two terminal device: Pins 1 and 3 shorted together and pins 4 and 6 shorted together.

## Recommended Operating Conditions

| Characteristic        | Symbol    | Min. | Typ. | Max. | Unit     |
|-----------------------|-----------|------|------|------|----------|
| Supply voltage        | $V_{AC}$  | —    | —    | 240  | $V_{ac}$ |
| Forward current       | $I_F$     | 15   | 20   | 25   | mA       |
| Peak on-state current | $I_{TP}$  | —    | —    | 1    | A        |
| Operating temperature | $T_{opr}$ | -25  | —    | 85   | °C       |

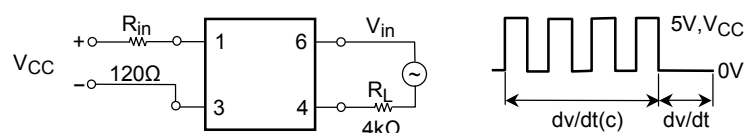
## Individual Electrical Characteristics (Ta = 25°C)

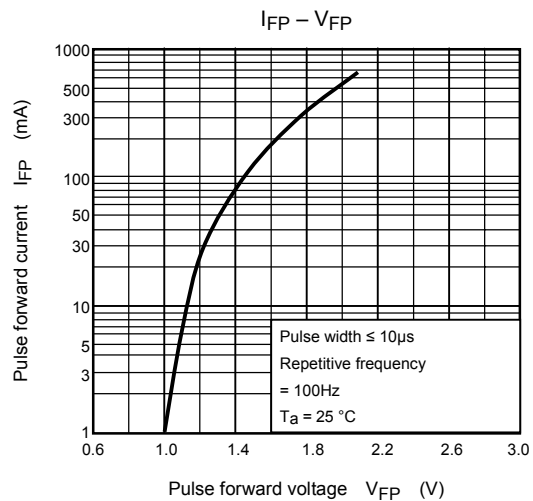
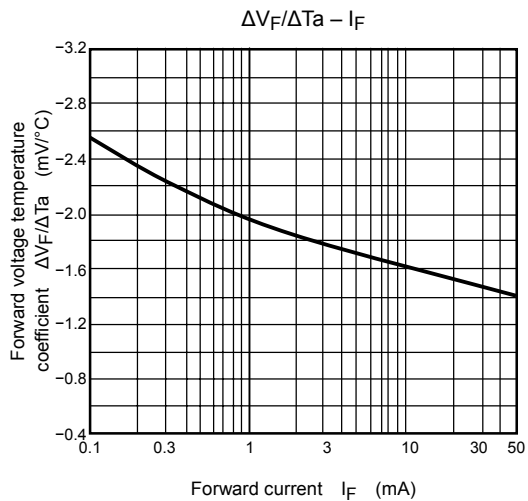
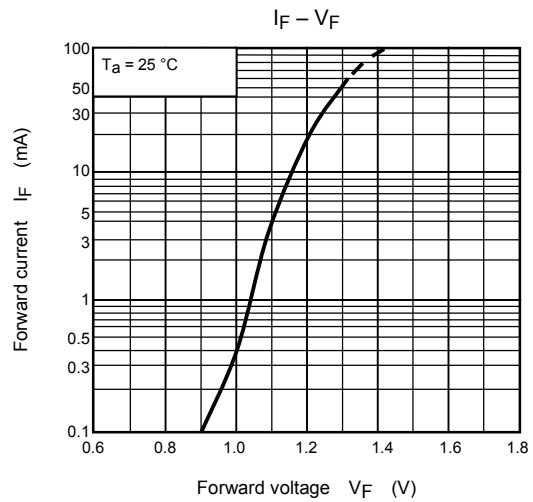
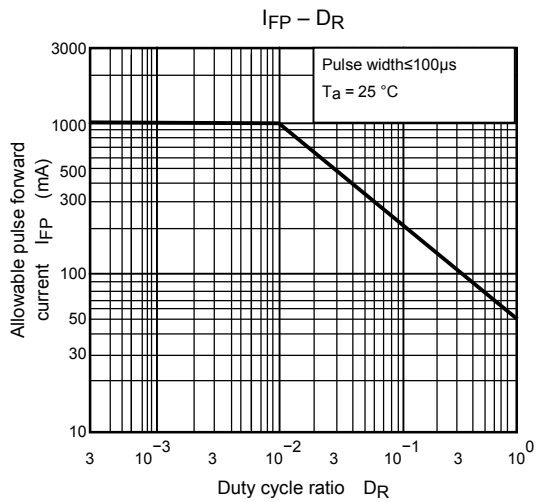
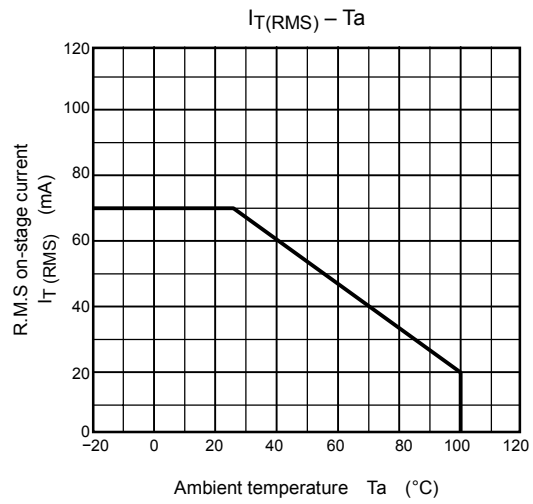
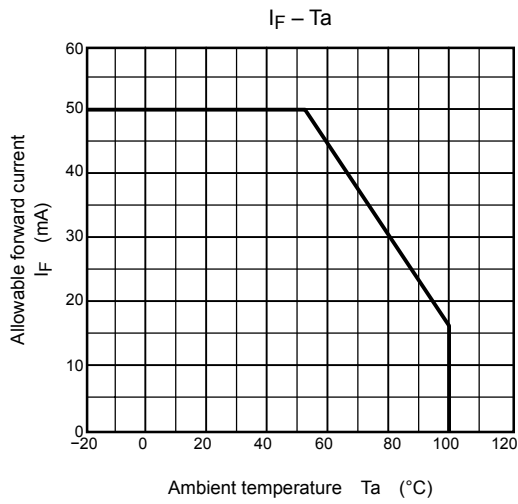
| Characteristic |  | Symbol           | Test Condition   | Min. | Typ. | Max. | Unit             |
|----------------|--|------------------|--|------|------|------|------------------|
| LED            | Forward voltage                              | $V_F$            | $I_F = 10\text{mA}$  | 1.0  | 1.15 | 1.3  | V                |
|                | Reverse current                              | $I_R$            | $V_R = 5\text{V}$  | —    | —    | 10   | $\mu\text{A}$    |
|                | Capacitance                                  | $C_T$            | $V = 0, f = 1\text{MHz}$   | —    | 30   | —    | pF               |
| Detector       | Peak off-state current                       | $I_{\text{DRM}}$ | $V_{\text{DRM}} = 600\text{V}$                                   | —    | 10   | 1000 | nA               |
|                | Peak on-state voltage                        | $V_{\text{TM}}$  | $I_{\text{TM}} = 70\text{mA}$                                    | —    | 1.7  | 2.8  | V                |
|                | Holding current                              | $I_H$            | —  | —    | 0.6  | —    | mA               |
|                | Critical rate of rise of off-state voltage   | $dv / dt$        | $V_{\text{in}} = 240\text{Vrms}, T_a = 85^\circ\text{C}$ (Fig.1) | 200  | 500  | —    | V/ $\mu\text{s}$ |
|                | Critical rate of rise of commutating voltage | $dv / dt(c)$     | $V_{\text{in}} = 60\text{Vrms}, I_T = 15\text{mA}$ (Fig.1)       | —    | 0.2  | —    | V/ $\mu\text{s}$ |

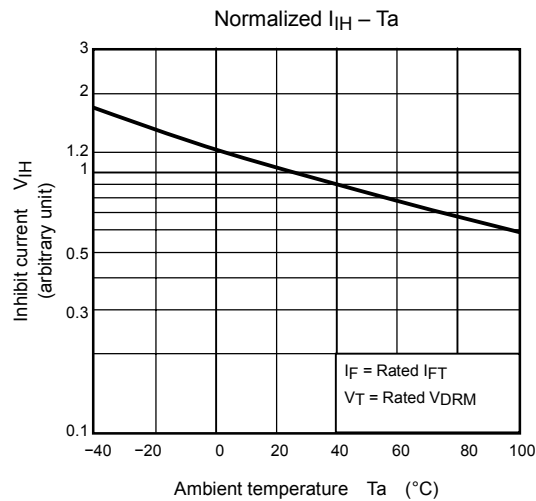
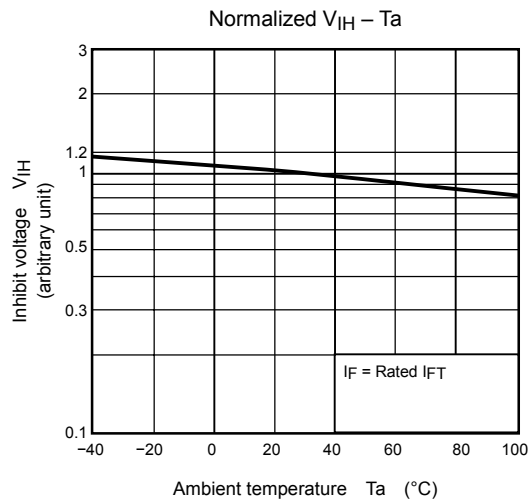
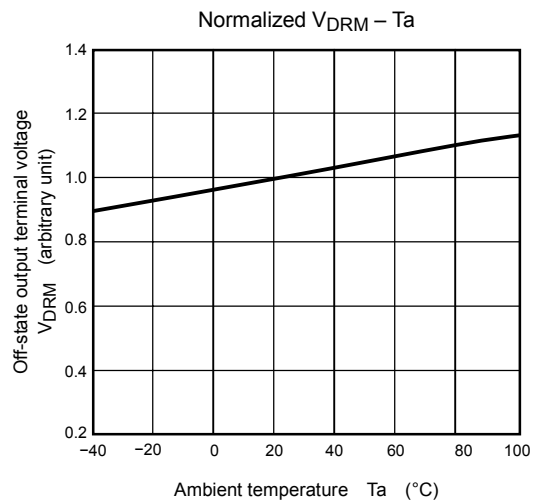
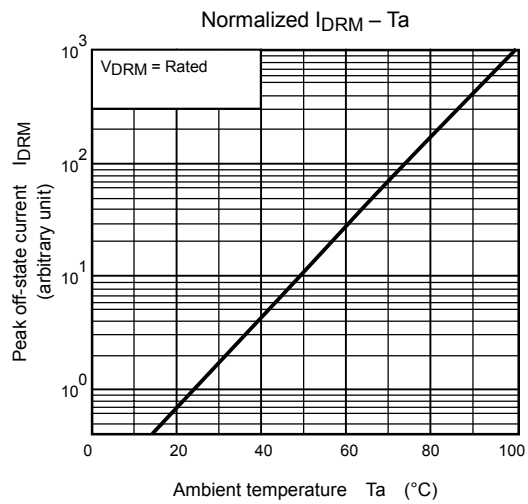
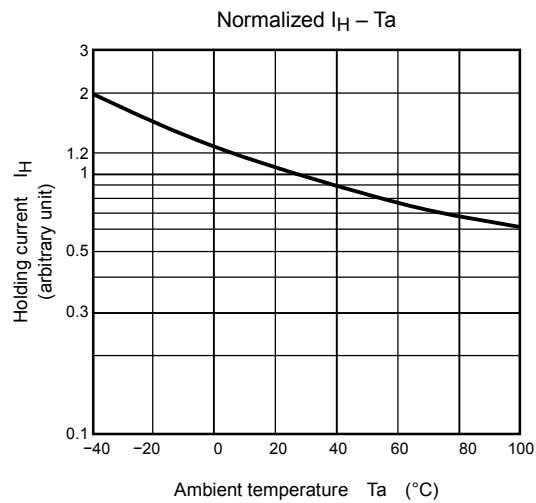
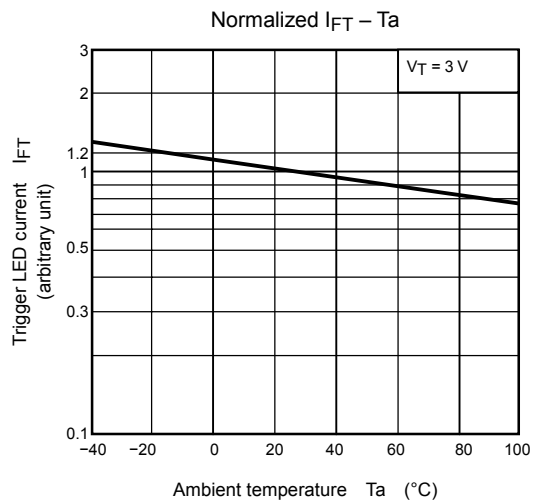
## Coupled Electrical Characteristics (Ta = 25°C)

| Characteristic                | Symbol          | Test Condition  | Min.               | Typ.      | Max. | Unit             |
|-------------------------------|-----------------|---|--------------------|-----------|------|------------------|
| Trigger LED current           | $I_{\text{FT}}$ | $V_T = 6\text{V}$   | —                  | 5         | 10   | mA               |
| Inhibit voltage               | $V_{\text{IH}}$ | $I_F = \text{Rated } I_{\text{FT}}$   | —                  | —         | 50   | V                |
| Leakage in inhibited state    | $I_{\text{IH}}$ | $I_F = \text{Rated } I_{\text{FT}}$<br>$V_T = \text{Rated } V_{\text{DRM}}$ | —                  | 200       | 600  | $\mu\text{A}$    |
| Capacitance (input to output) | $C_S$           | $V_S = 0, f = 1\text{MHz}$  | —                  | 0.8       | —    | pF               |
| Isolation resistance          | $R_S$           | $V_S = 500\text{V}, \text{R.H.} \leq 60\%$                                  | $1 \times 10^{12}$ | $10^{14}$ | —    | $\Omega$         |
| Isolation voltage             | $BV_S$          | AC, 1 minute  | 2500               | —         | —    | $V_{\text{rms}}$ |
|                               |                 | AC, 1 second, in oil  | —                  | 5000      | —    |                  |
|                               |                 | AC, 1 minute, in oil  | —                  | 5000      | —    | Vdc              |

Fig.1 dv / dt test circuit







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000707EBC

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